

Title (en)

Method for manufacturing a MEMS/NEMS electromechanical component in a monocrystalline material

Title (de)

Verfahren zur Herstellung eines elektromechanischen MEMS-Bauteils in einem einkristallinen Material

Title (fr)

Procédé de fabrication d'un composant électromécanique MEMS/NEMS dans un matériau monocristallin

Publication

EP 2138451 B1 20110525 (FR)

Application

EP 09290471 A 20090622

Priority

FR 0803494 A 20080623

Abstract (en)

[origin: EP2138451A1] The method involves realizing a heterogeneous substrate with a part composed of single-crystal silicon layers (1, 3) and a mechanical layer (6), where the layer (6) is extended till a sacrificial interface layer (8) realized by phosphor silicate glass or silica. Openings (20) are formed from a surface of the part, where the openings are opened on buried zones (2-1, 3-1, 5-1). The buried zones are partially engraved to form a cavity in a manner to define an active element that is a part of the layer (6) between the cavity and the interface layer.

IPC 8 full level

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CPC (source: EP US)

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